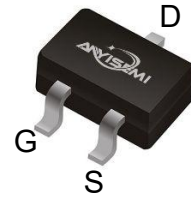


### Description

The SI2310A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



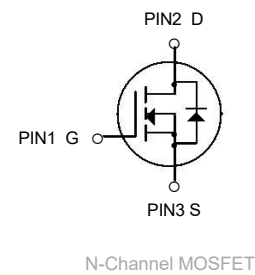
### General Features

$V_{DS} = 60V$   $I_D = 3A$   
 $R_{DS(ON)} < 85m\Omega @ V_{GS}=10V$

**SOT-23**

### Application

- Battery protection
- Load switch
- Uninterruptible power supply



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SI2310A	SOT-23	S10	3000PCS

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	3	A
$I_{DM}$	Drain Current-Pulsed <sup>(Note 1)</sup>	10	A
$P_D$	Maximum Power Dissipation	1.7	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	73.5	$^\circ C/W$

**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1.3	2.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	72	85	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.5A	-	85	103	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =2A		3	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	510	-	PF
Output Capacitance	C <sub>oss</sub>		-	34	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	26	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =1.5A V <sub>GS</sub> =10V, R <sub>GEN</sub> =1Ω	-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =3A, V <sub>GS</sub> =4.5V	-	7.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	3	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

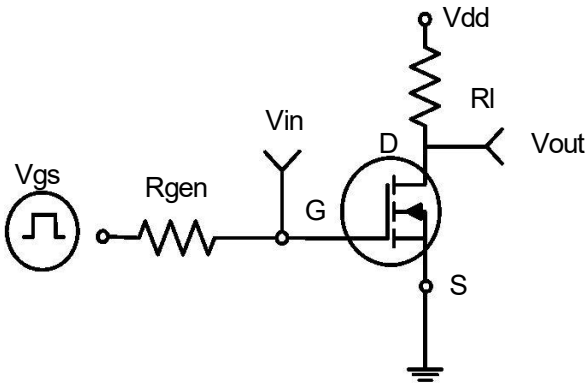


Figure 1: Switching Test Circuit

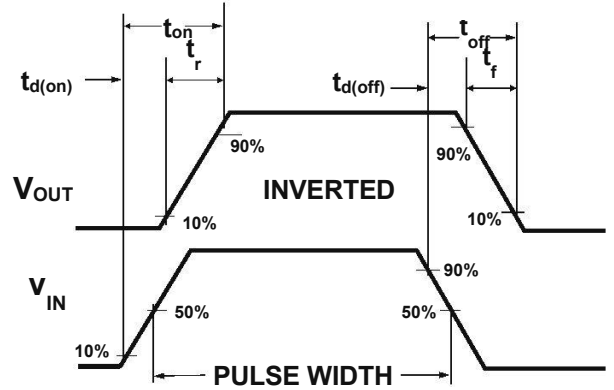


Figure 2: Switching Waveforms

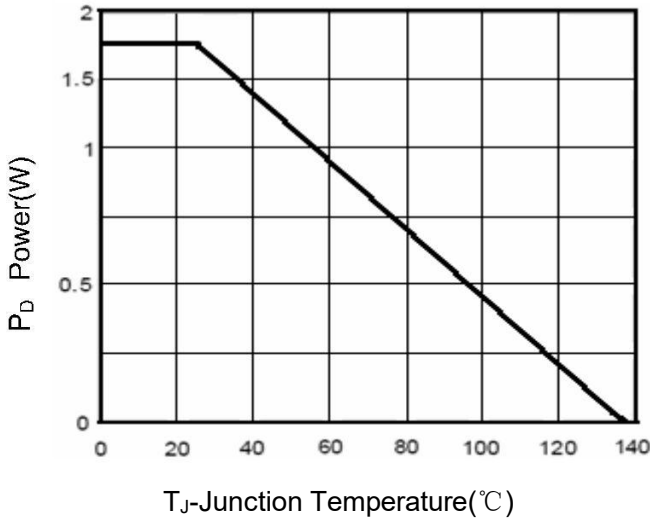


Figure 3 Power Dissipation

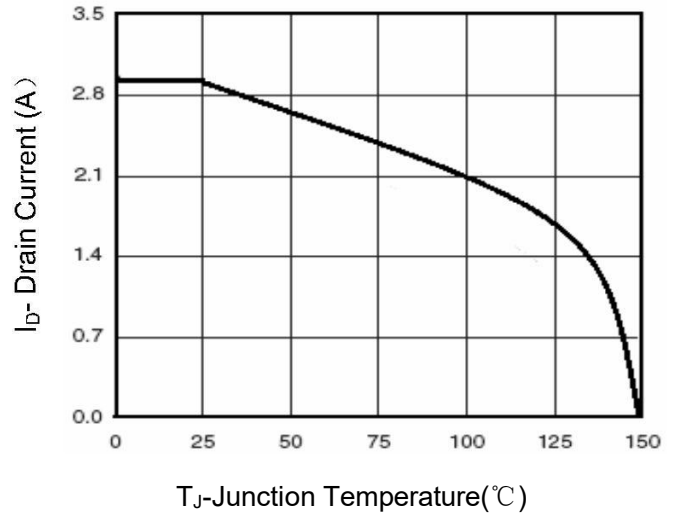


Figure 4 Drain Current

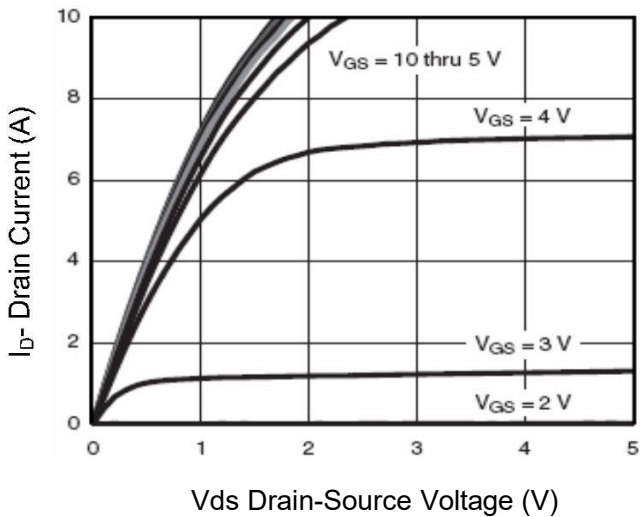


Figure 5 Output Characteristics

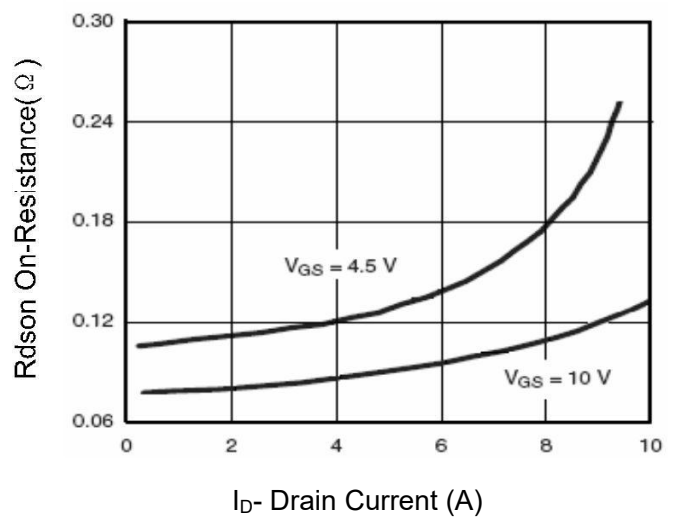
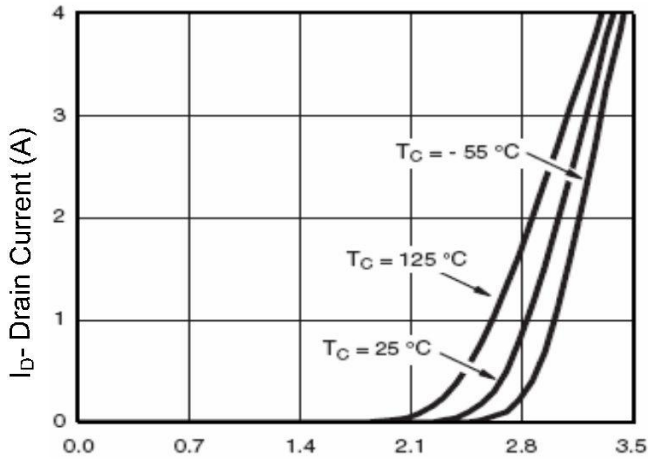
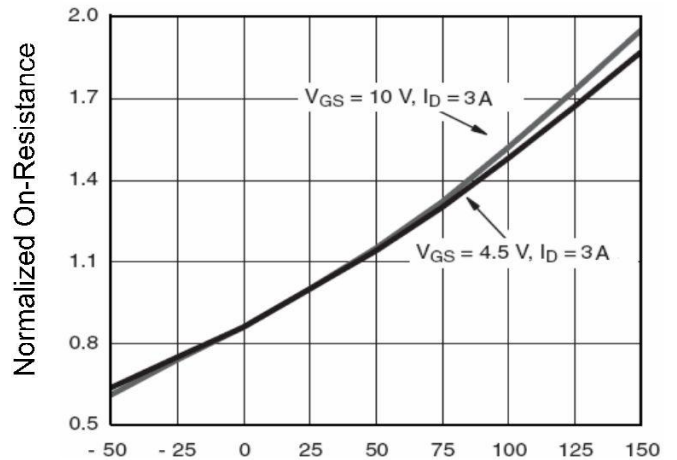


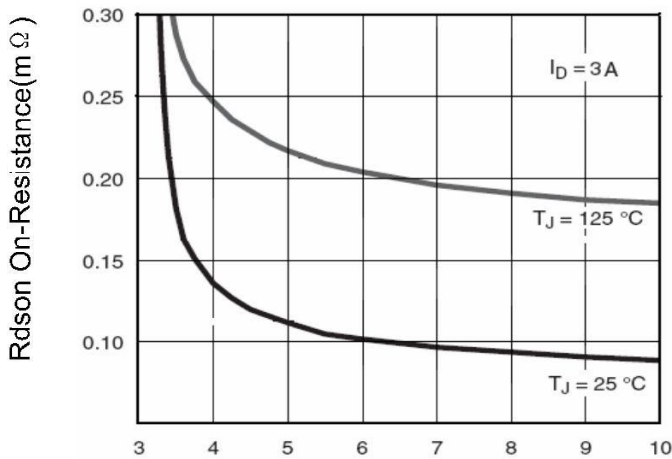
Figure 6 Drain-Source On-Resistance



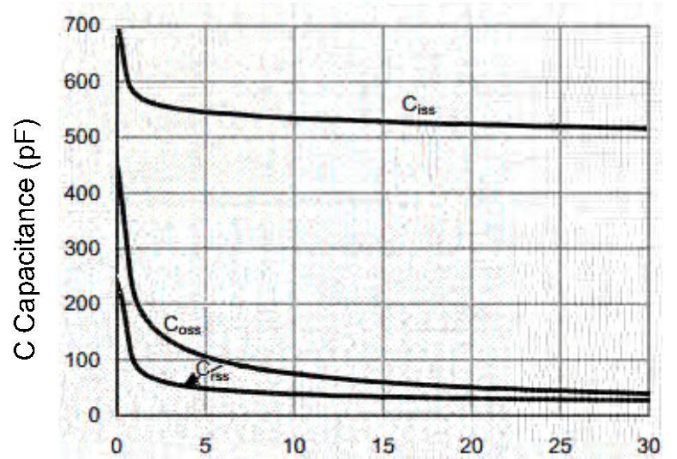
Vgs Gate-Source Voltage (V)  
**Figure 7 Transfer Characteristics**



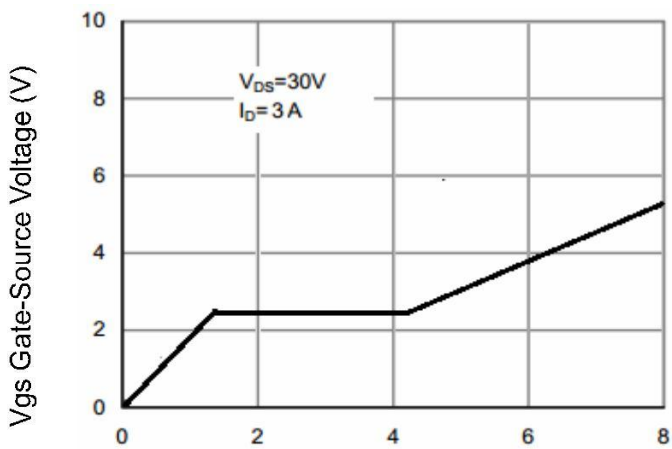
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 8 Drain-Source On-Resistance**



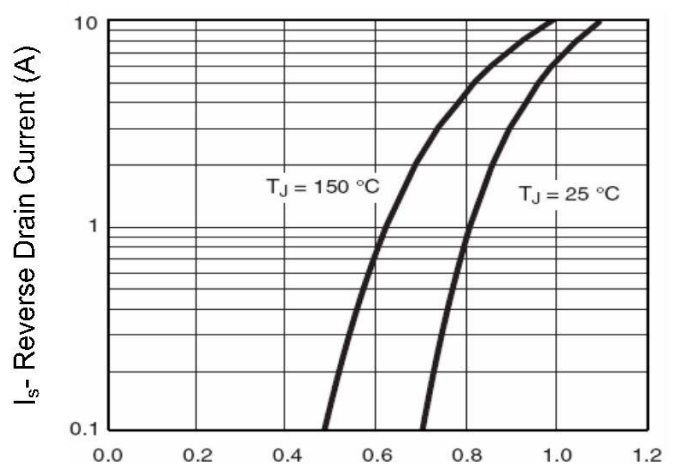
Vgs Gate-Source Voltage (V)  
**Figure 9 Rdson vs Vgs**



Vds Drain-Source Voltage (V)  
**Figure 10 Capacitance vs Vds**



Qg Gate Charge (nC)  
**Figure 11 Gate Charge**



Vsd Source-Drain Voltage (V)  
**Figure 12 Source- Drain Diode Forward**

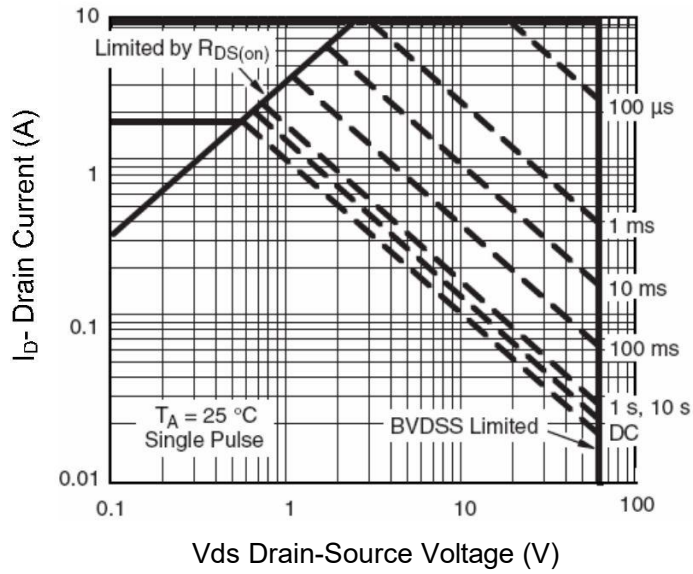


Figure 13 Safe Operation Area

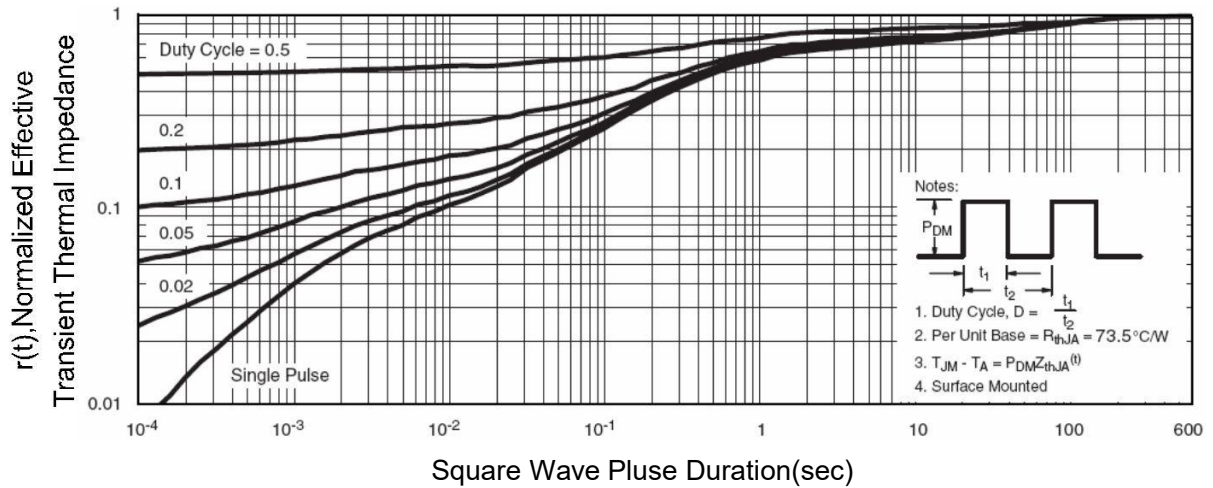
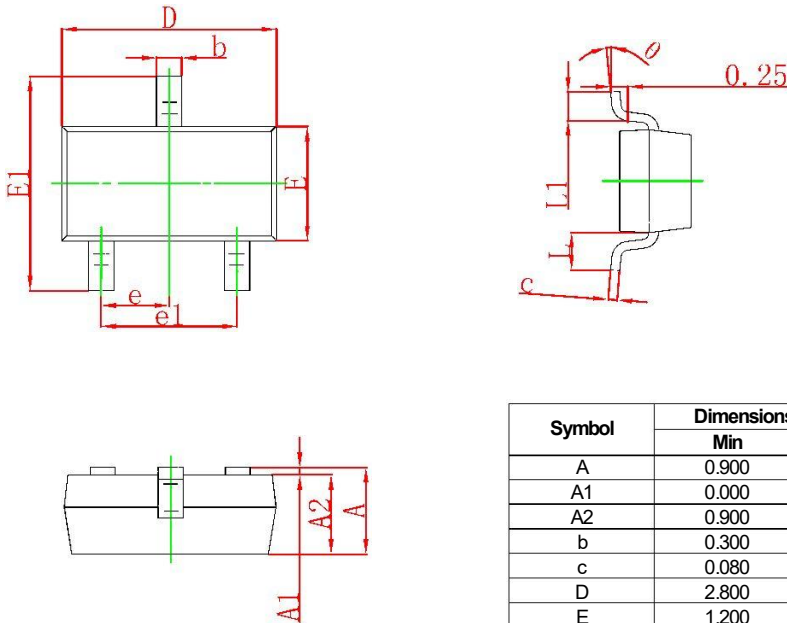


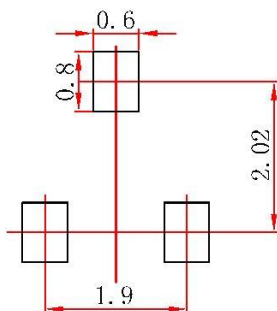
Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ± 0.05mm.  
 3. The pad layout is for reference purposes only.

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